



Part Number :		Date:	07 Mar 2005
Customer:		STD:	Y
Customer Specification/ Reference:			

Category	Parameter	Specification	Measurement Method
<i>Overall</i>			
<i>Wafer</i>			
1.1	Diameter	150mm +/- 0.5	Wafer Vendor
1.2	Primary Flat Orientation	{110}+/- 1°	Wafer Vendor
1.3	Primary Flat Length	57.5mm +/- 2.5	Wafer Vendor
1.4	Secondary Flat Orientation	None	
1.5	Thickness	745 µm +/- 6	Guaranteed by Process
1.6	Total Thickness Variation(TTV)	< 5µm	Guaranteed by Process
1.7	Bow	< 60 µm	ADE to ASTM F534, 20%
1.8	Warp	< 60 µm	ADE to ASTM F657, 20%
1.9	Edge Chips	0	Bright Light, 100% ¹
1.10	Edge Exclusion	5mm	
<i>Handle</i>			
<i>Silicon</i>			
2.1	Growth Method	CZ	Wafer Vendor
2.2	Orientation	{100}+/- 1°	Wafer Vendor
2.3	Thickness	625µm +/- 5µm	ADE, 100%
2.4	Doping type	N	Wafer Vendor
2.5	Dopant	Phosphorous	Wafer Vendor
2.6	Resistivity	1-10 ohm-cm	Wafer Vendor
2.7	Backside Finish	Lapped & etched with oxide & laser ID mark	Guaranteed by Process
<i>Buried</i>			
<i>Oxide</i>			
3.1	Oxide Type	Thermal	
3.2	Oxide Thickness	500 nm +/- 15nm	Nanospec centre point, 4%
3.3	Oxide formed on	Handle Wafer	

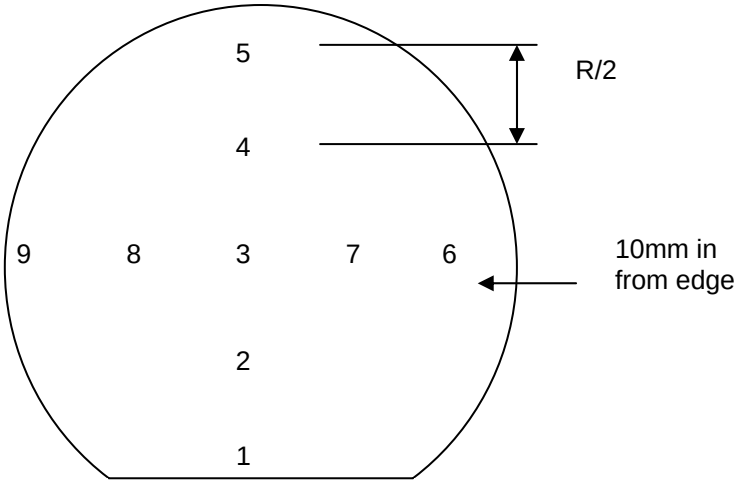
Category	Parameter	Specification	Measurement Method
<i>Device</i>			
<i>Silicon</i>			
4.1	Growth Method	CZ	Wafer Vendor
4.2	Orientation	{100}+/- 1°	Wafer Vendor
4.3	Nominal Thickness	120 µm	FTIR / ADE, 100%, 9 Point
4.4	Thickness Variation	+/- 1.0µm	FTIR/ ADE, 100% 9 point
4.5	Distance to device silicon		
	edge from wafer edge	<2mm	Typical by process
4.6	Doping Type	N	Wafer Vendor
4.7	Dopant	Phosphorous	Wafer Vendor
4.8	Resistivity	1 - 10 ohm-cm	Wafer Vendor
4.9	Final Field Oxidation	None	Nanospec centre point, 4%
4.10	Voids	0	Bright Light, 100% ¹
4.11	Device Side Scribe	None	
4.12	Scratches	none	Bright Light, 100% ¹
4.13	Haze	None	Bright Light, 100% ¹
4.14	Particles	<30 @ 0.3um	Tencor 6220

Shipping
Details

Wafers per box	MAX 25
Packaging	Taped Polypropylene Wafer Box Empak, Ultrapak, 150mm Antistatic Double Bagging
Lot Shipment Data :	Device Silicon Thickness Bow/Warp Data

Explanatory Notes

1. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in 1.10. High intensity bright lamp inspection as per ASTM F523.
2. 9 point measurement is centre and 4 points 10mm from edge of wafer.



Approvals:	Quality:	Engineering:
	Marketing:	TRB:
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